



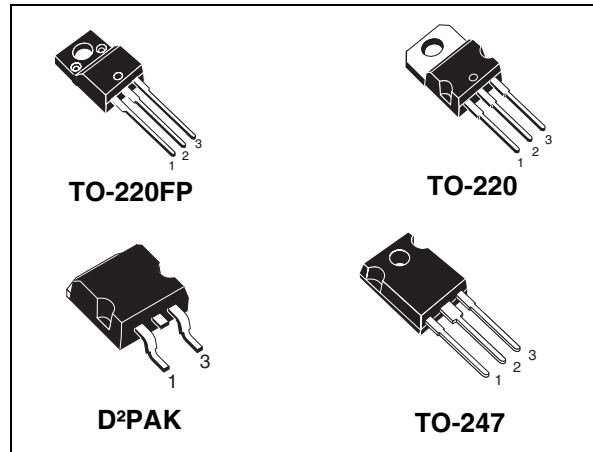
STB28NM50N, STF28NM50N STP28NM50N, STW28NM50N

N-channel 500 V, 0.135 Ω , 21 A D²PAK, TO-220, TO-220FP, TO-247
MDmesh™ II Power MOSFET

Features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)} max	I _D
STB28NM50N	550 V	< 0.158 Ω	21 A
STF28NM50N			
STP28NM50N			
STW28NM50N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Application

Switching applications

Description

These devices are made using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

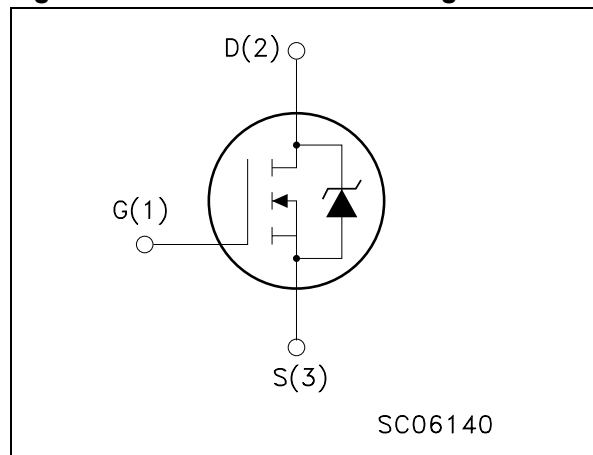


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB28NM50N	28NM50N	D ² PAK	Tape and reel
STF28NM50N		TO-220FP	Tube
STP28NM50N		TO-220	
STW28NM50N		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	5
2.1	Electrical characteristics (curves)	7
3	Test circuits	10
4	Package mechanical data	11
5	Packaging mechanical data	16
6	Revision history	17

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-220FP	TO-247	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	500				V
V_{GS}	Gate- source voltage	± 25				V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	21		21 ⁽¹⁾	21	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	13		13 ⁽¹⁾	13	A
$I_{DM}^{(2)}$	Drain current (pulsed)	84		84 ⁽¹⁾	84	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	90		25	150	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}; T_C=25\text{ °C}$)			2500		V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	21				V/ns
T_{stg}	Storage temperature	- 55 to 150				°C
T_j	Max. operating junction temperature	150				°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 21\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-247	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	1.39		0.83	5	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		50	62.5	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max		30			°C/W
T_l	Maximum lead temperature for soldering purpose	300		300		°C

- When mounted on 1inch² FR-4 board, 2 oz Cu

Electrical ratings**STB28NM50N, STF28NM50N, STP28NM50N, STW28NM50N****Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max)	8.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	430	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}, @125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 10.5 \text{ A}$		0.135	0.158	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz},$ $V_{GS} = 0$	-	1735	-	pF
C_{oss}	Output capacitance			122		pF
C_{rss}	Reverse transfer capacitance			4.3		pF
$C_{oss(tr)}^{(1)}$	Equivalent output capacitance time related	$V_{GS} = 0, V_{DS} = 0 \text{ to } 50 \text{ V}$	-	122	-	pF
$C_{oss(er)}^{(2)}$	Equivalent output capacitance energy related			86		
Q_g	Total gate charge	$V_{DD} = 400 \text{ V}, I_D = 21 \text{ A},$ $V_{GS} = 10 \text{ V},$ (see Figure 18)	-	50	-	nC
Q_{gs}	Gate-source charge			9.5		nC
Q_{gd}	Gate-drain charge			25		nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain	-	2.7	-	Ω

- $C_{oss(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- $C_{oss(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical characteristics

STB28NM50N, STF28NM50N, STP28NM50N, STW28NM50N

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250\text{ V}$, $I_D = 10.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17)		13.6		ns	
t_r	Rise time			19		ns	
$t_{d(off)}$	Turn-off delay time				62		ns
t_f	Fall time				52		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		21	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				84	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 21\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$ (see Figure 22)	-	326		ns
Q_{rr}	Reverse recovery charge			5		μC
I_{RRM}	Reverse recovery current			30		A
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 22)	-	376		ns
Q_{rr}	Reverse recovery charge			6.2		μC
I_{RRM}	Reverse recovery current			33.2		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

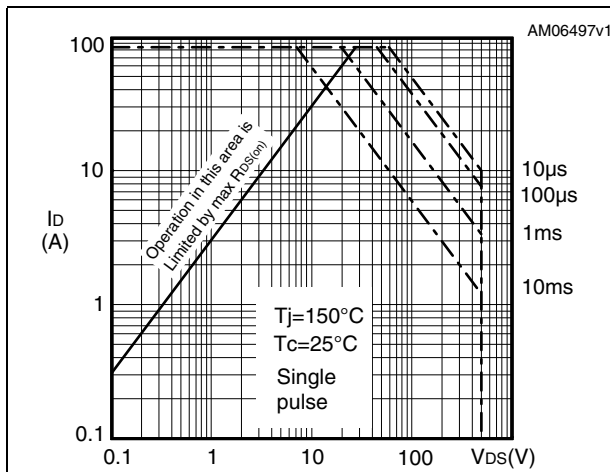


Figure 3. Thermal impedance for TO-220, D²PAK

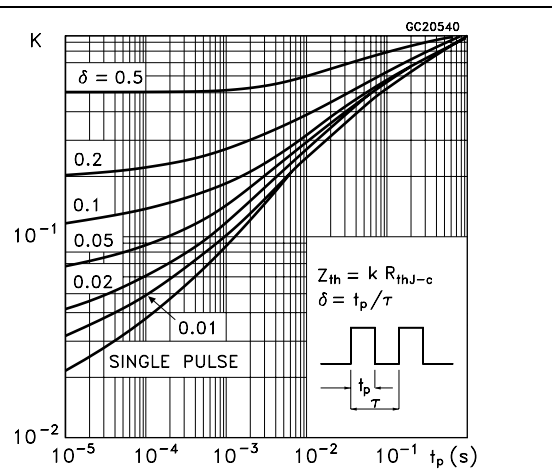


Figure 4. Safe operating area for TO-220FP

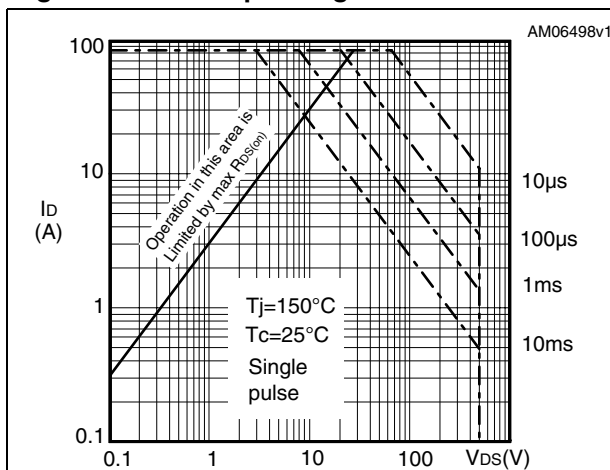


Figure 5. Thermal impedance for TO-220FP

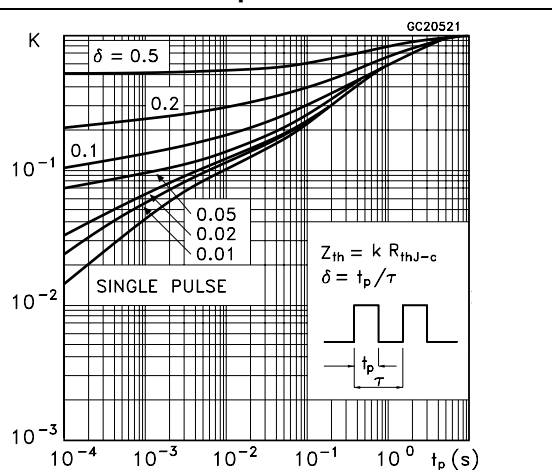


Figure 6. Safe operating area for TO-247

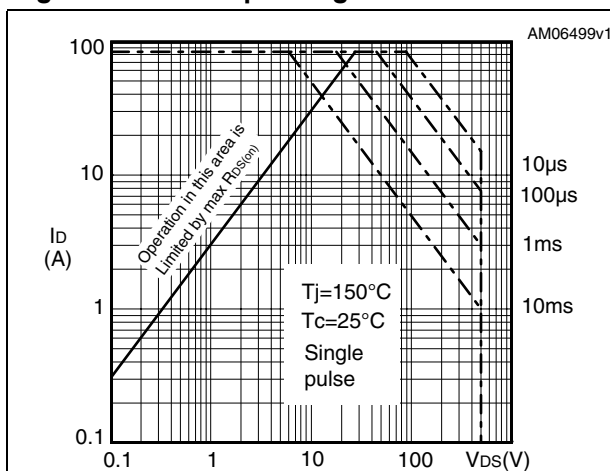
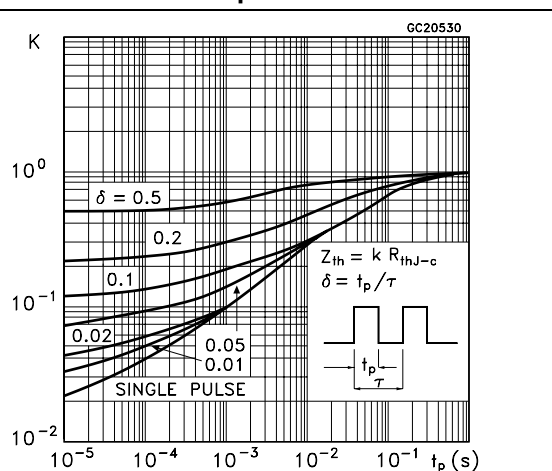


Figure 7. Thermal impedance for TO-247



Electrical characteristics

STB28NM50N, STF28NM50N, STP28NM50N, STW28NM50N

Figure 8. Output characteristics

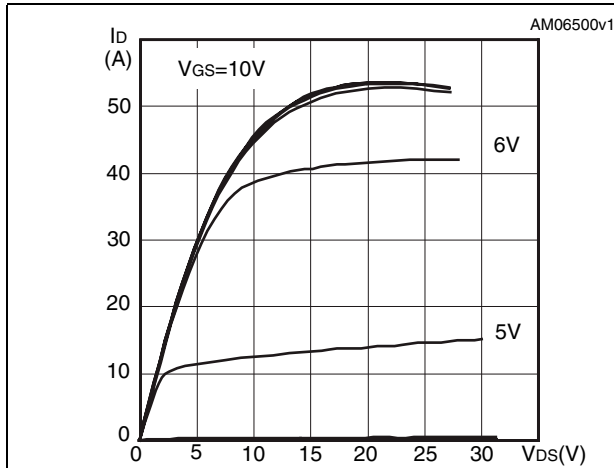


Figure 9. Transfer characteristics

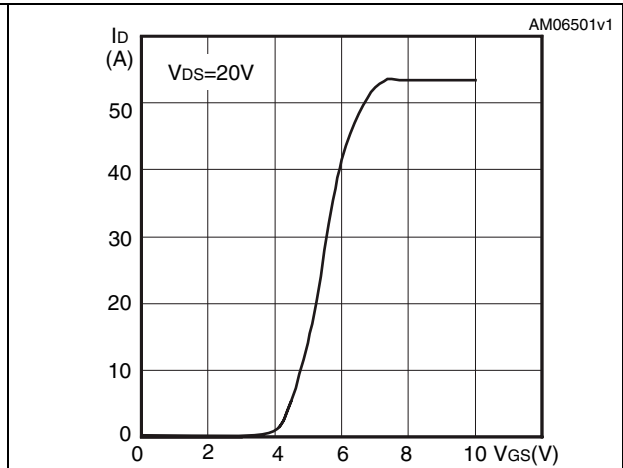


Figure 10. Gate charge vs gate-source voltage Figure 11. Static drain-source on resistance

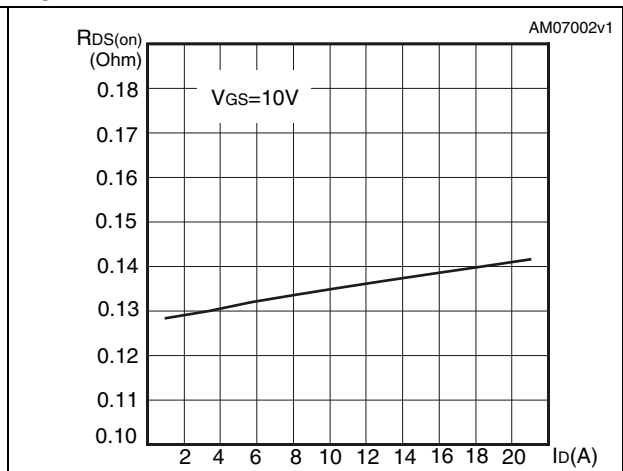
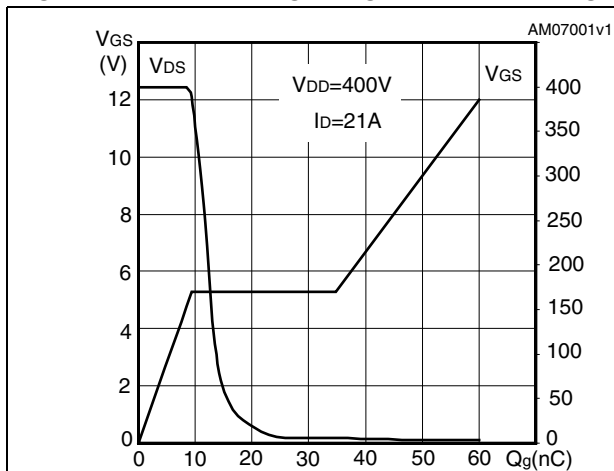


Figure 12. Capacitance variations

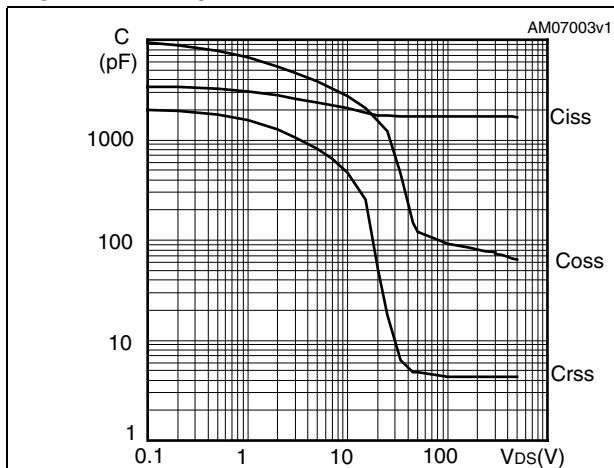


Figure 13. Output capacitance stored energy

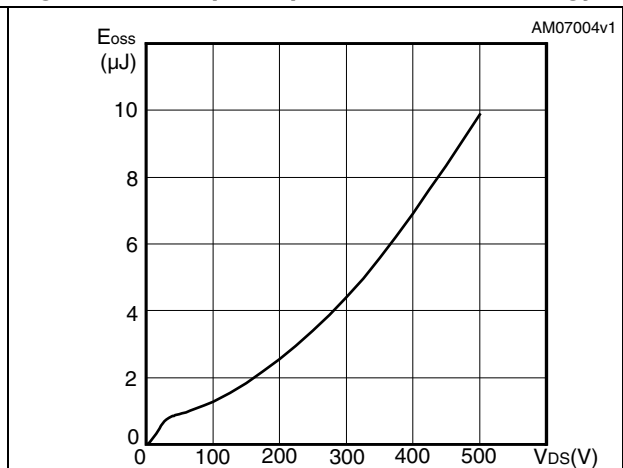


Figure 14. Normalized gate threshold voltage vs temperature

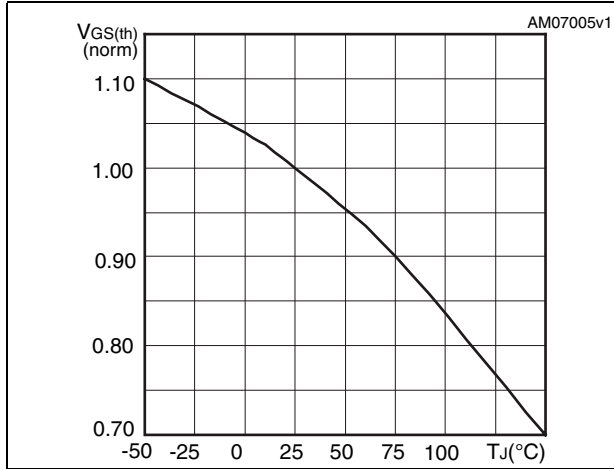


Figure 15. Normalized on resistance vs temperature

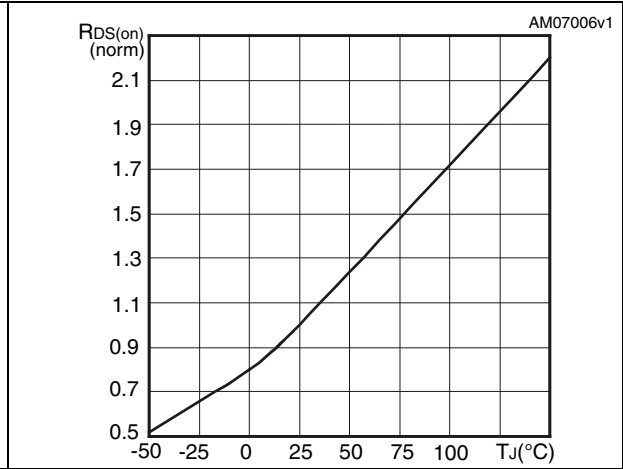
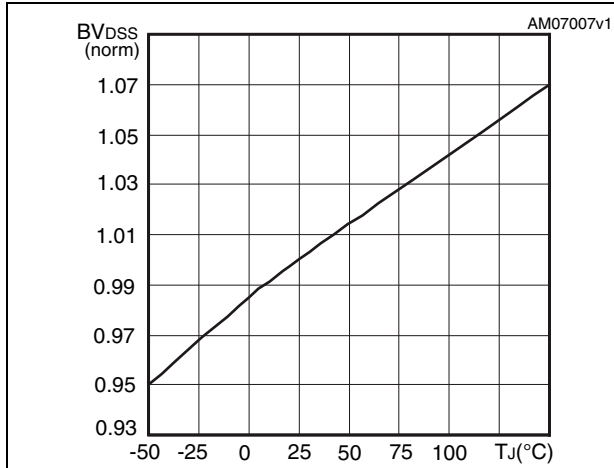


Figure 16. Normalized B_{VDSS} vs temperature



3 Test circuits

Figure 17. Switching times test circuit for resistive load

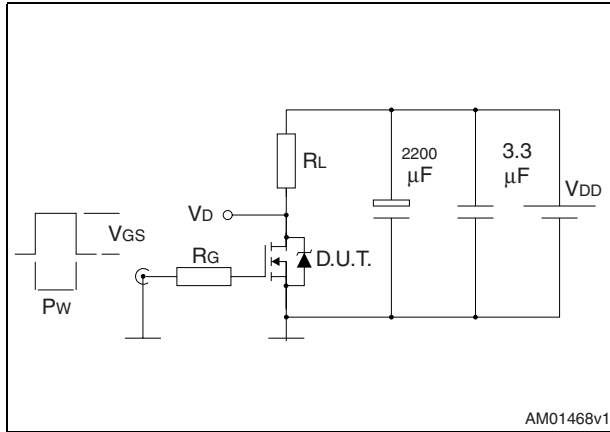


Figure 18. Gate charge test circuit

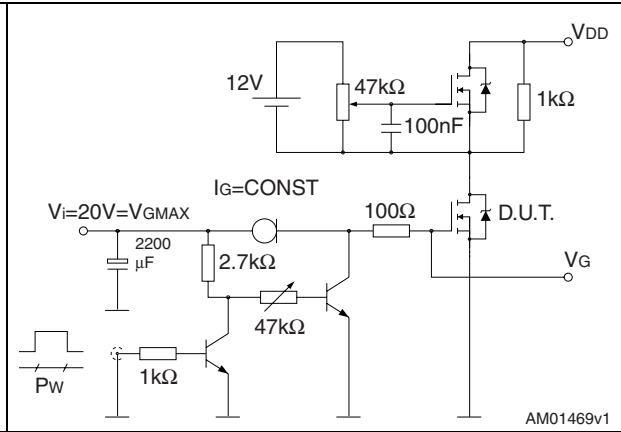


Figure 19. Test circuit for inductive load switching and diode recovery times

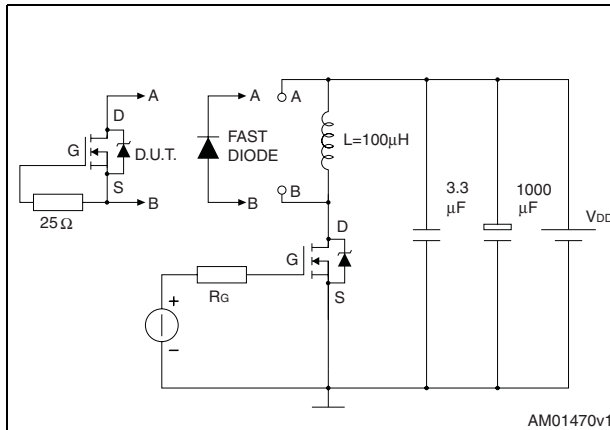


Figure 20. Unclamped inductive load test circuit

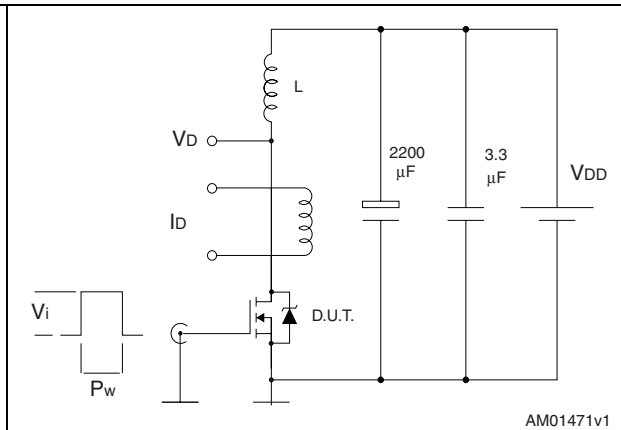


Figure 21. Unclamped inductive waveform

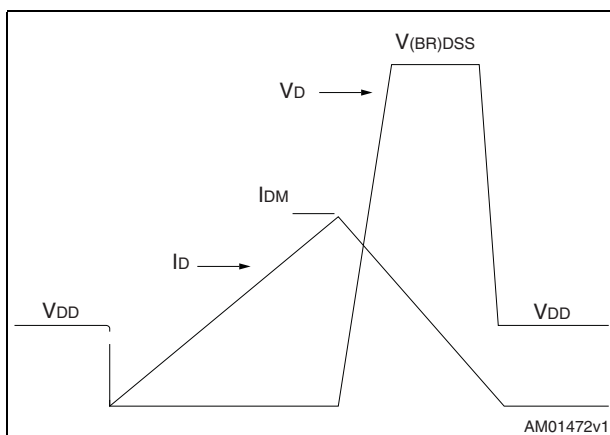
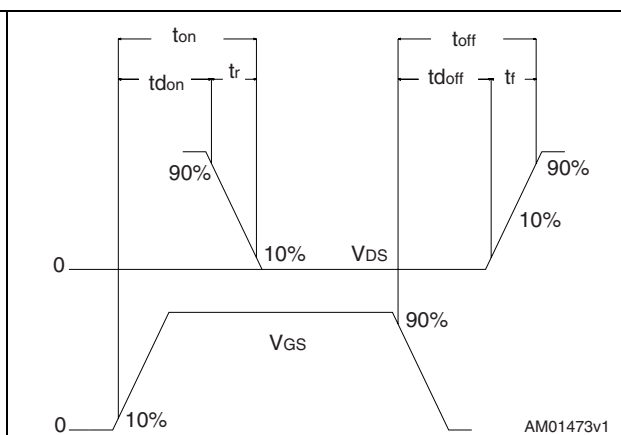


Figure 22. Switching time waveform



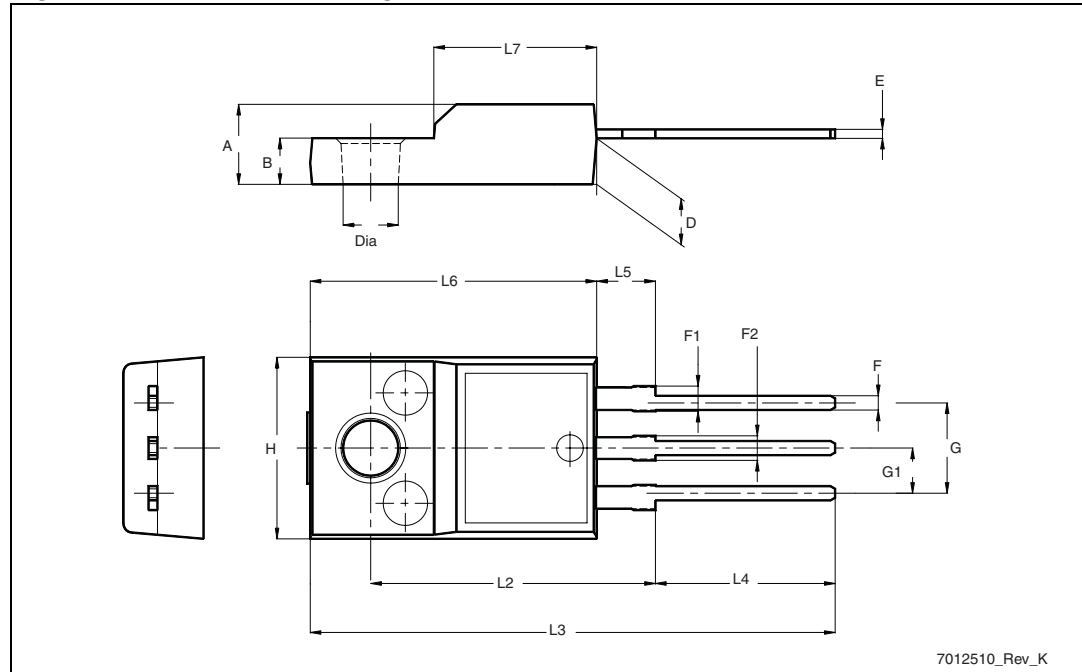
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

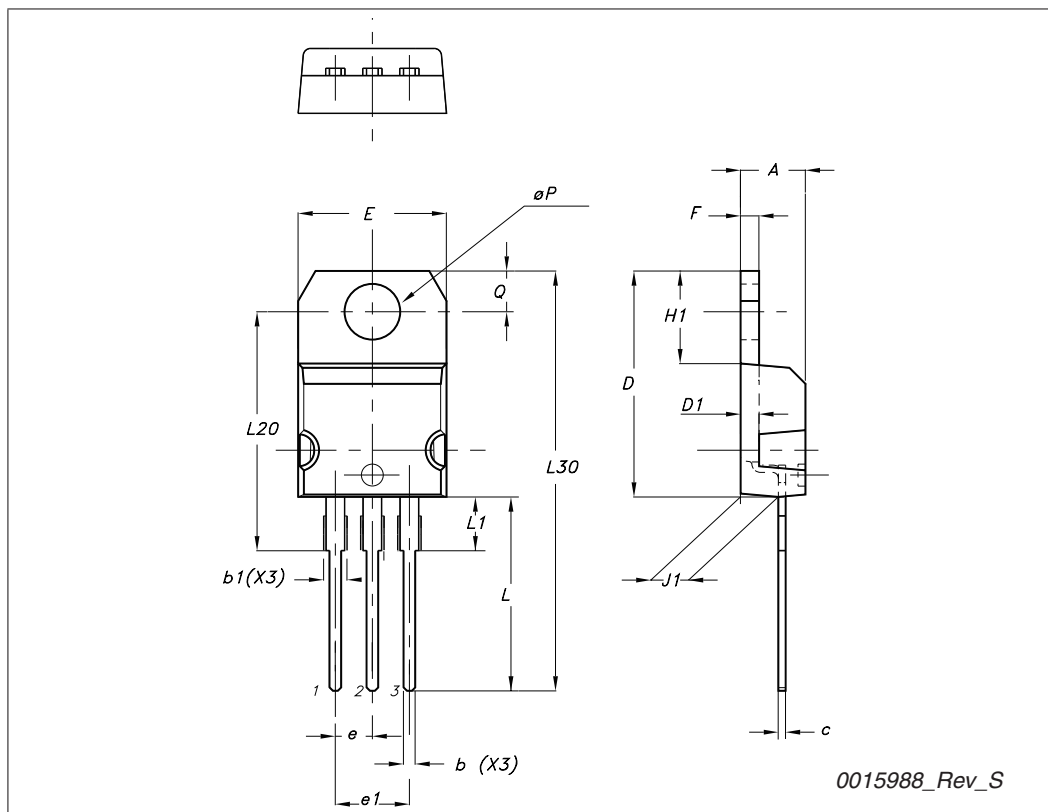
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing



TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95

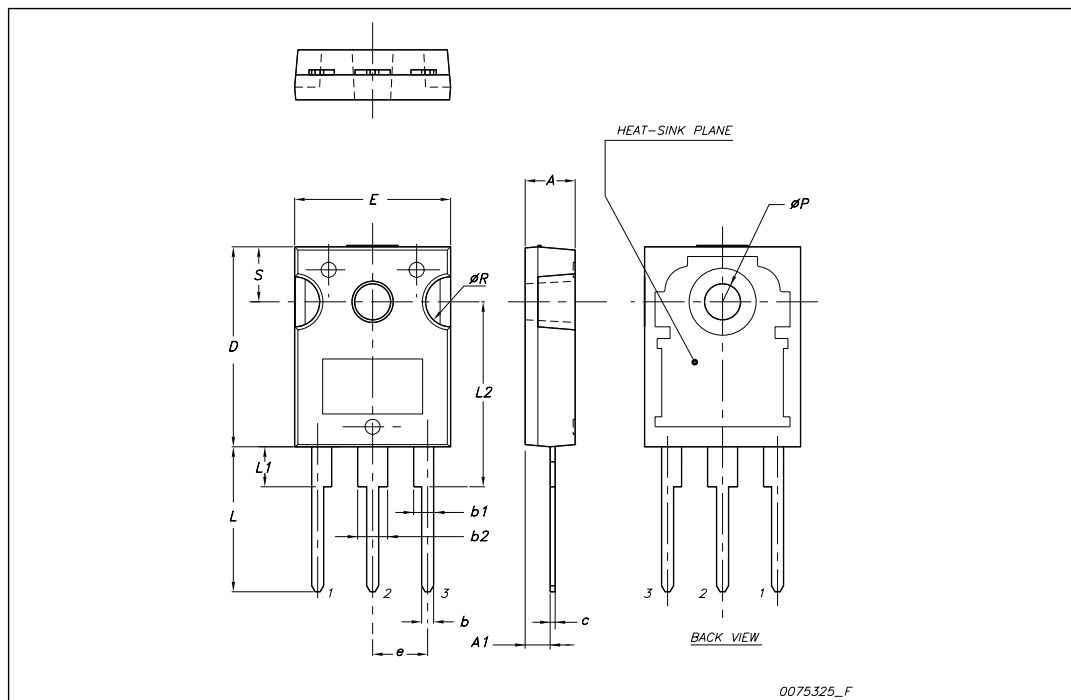


Package mechanical data

STB28NM50N, STF28NM50N, STP28NM50N, STW28NM50N

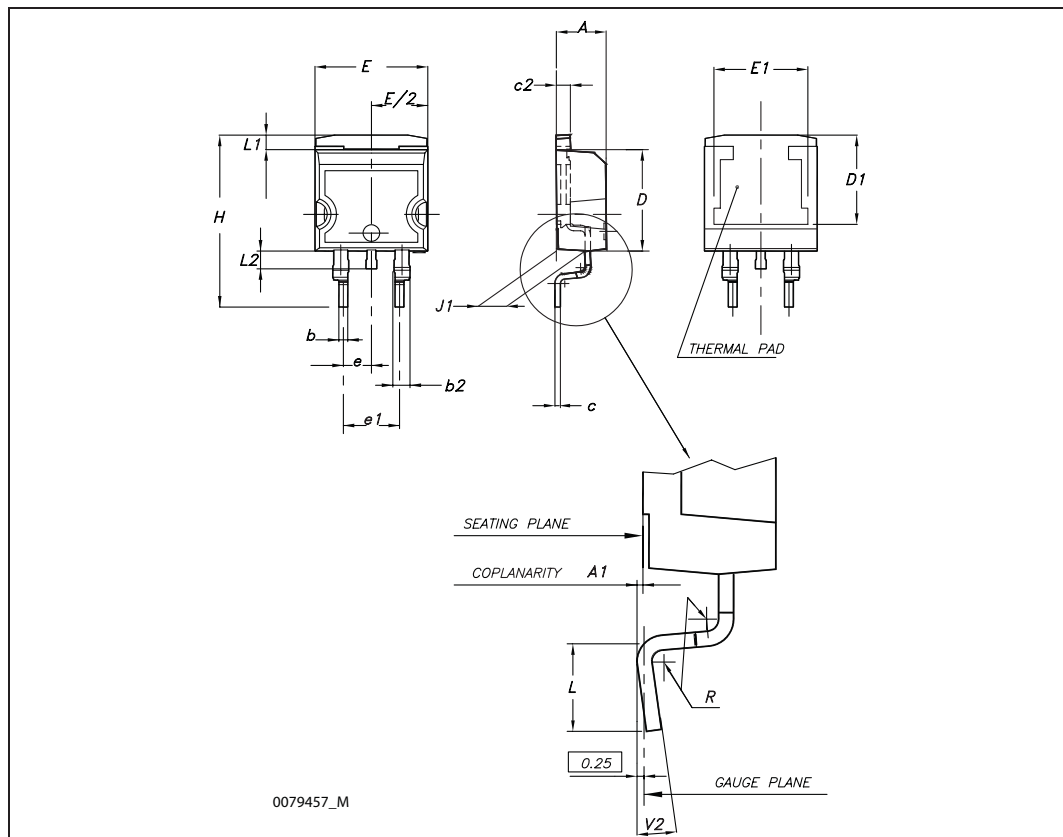
TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



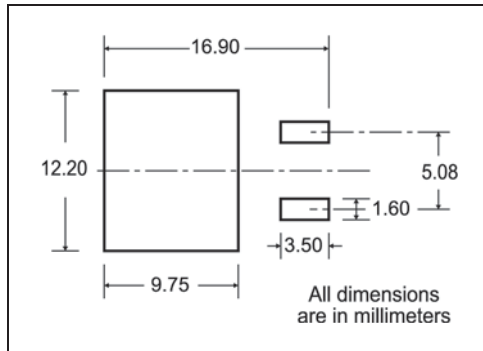
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

6 Revision history

Table 10. Document revision history

Date	Revision	Changes
19-Jul-2010	1	First release.

STB28NM50N, STF28NM50N, STP28NM50N, STW28NM50N

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com